

# Photo IC for laser beam synchronous detection **S10456**

Stable timing output with small variations in propagation delay time



S10456 photo IC uses a dual-element Si PIN photodiode and compares the two signals to obtain a highly stable output. S10456 shows small variations in the propagation delay time even when laser power fluctuates, so that stable timing is output.

## Features

- High sensitivity  
Current amplifier gain: 20 times
- Stable timing output (less than  $\pm 4$  ns) even if input power varies by more than 4 times
- Digital output
- Small package
- Active area (PD1: 2.5 × 0.3 mm, PD2: 2.5 × 0.5 mm)
- Suitable for lead-free reflow (RoHS compliance)

## Applications

- Print start timing detection for laser printers, digital copiers, fax machines, etc.

### ■ Absolute maximum ratings (Ta=25 °C)

Parameter	Symbol	Value	Unit
Supply voltage	Vcc	-0.5 to +7	V
Power dissipation *1	P	300	mW
Output voltage *2	Vo	-0.5 to +7	V
Output current	Io	5	mA
Ro1, Ro2 terminal current	IRO	5	mA
Operating temperature	Topr	-25 to +80	°C
Storage temperature	Tstg	-40 to +85	°C

\*1: Power dissipation decreases at a rate of 4 mW/°C above Ta=25 °C

\*2: Vcc=+0.5 V or less

### ■ Electrical and optical characteristics (Ta=25 °C, $\lambda$ =780 nm, Vcc=5 V, Ro1=Ro2=1.5 kΩ, unless otherwise noted)

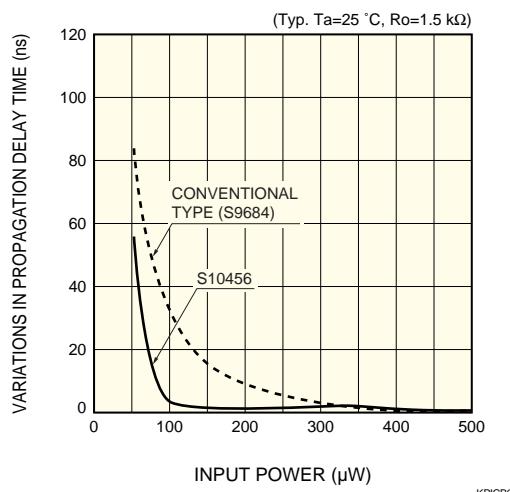
Parameter	Symbol	Condition	Min.	Typ.	Max.	Unit
Current consumption	Icc	Pi=0	-	-	10	mA
High level output voltage	VOH	Pi=0	4.6	-	-	V
Low level output voltage	VOL	IoL=4 mA, Pi=250 μW	-	-	0.4	V
Threshold input power	PTH		30	45	67	μW
Analog amplitude	VRO	*3	1.6	2.0	2.4	V
Propagation delay time variation	ΔtP	Pi=100 μW to 400 μW *4	-	-	$\pm 4$	ns
Rise time	tr	CL=15 pF	-	-	200	ns
Fall time	tf		-	-	100	ns
Maximum input power	Pi Max.		-	-	$PTH \times 8$	μW

\*3: Voltage change at Ro2 terminal when irradiated with laser beam of Pi=150 μW

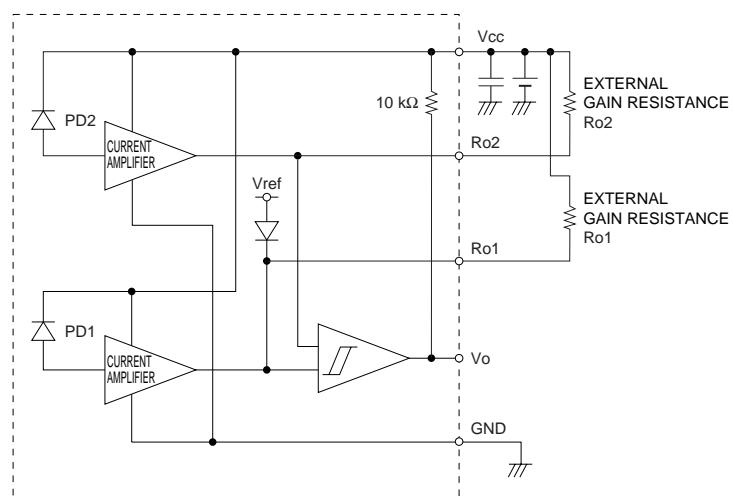
\*4: Beam diameter ( $1/e^2$ )=55 μm, scan speed=1.18 mm/μs

Not including jitter caused by polygon mirror non-uniformity

■ Variations in propagation delay time vs. input power



■ Block diagram



■ Functions

S10456 photo IC integrates a photodiode chip and an IC chip into the same package. The photodiode chip is internally connected to the IC chip as shown in the block diagram. S10456 should be used with terminals Ro1 and Ro2 connected to an external gain resistance.

Laser beams must be scanned in the direction from the 0.3 mm wide photodiode toward the 0.5 mm wide photodiode.

Two photocurrents are generated when a laser beam enters the dual-element photodiode. Each photocurrent is fed to the input terminal of the IC and, after being amplified by the current amplifier, flows to the external gain resistance. At this time, voltages VRO1 and VRO2 at terminals Ro1 and Ro2 are given by the following expression.

$$V_{RO1} (V_{RO2}) = V_{CC} - A \times S \times P_I \times R_{O1} (R_{O2}) [V]$$

A: Current amplifier gain (20 times)

S: Photo sensitivity of photodiode [A/W] (approx. 0.45 A/W at 780 nm)

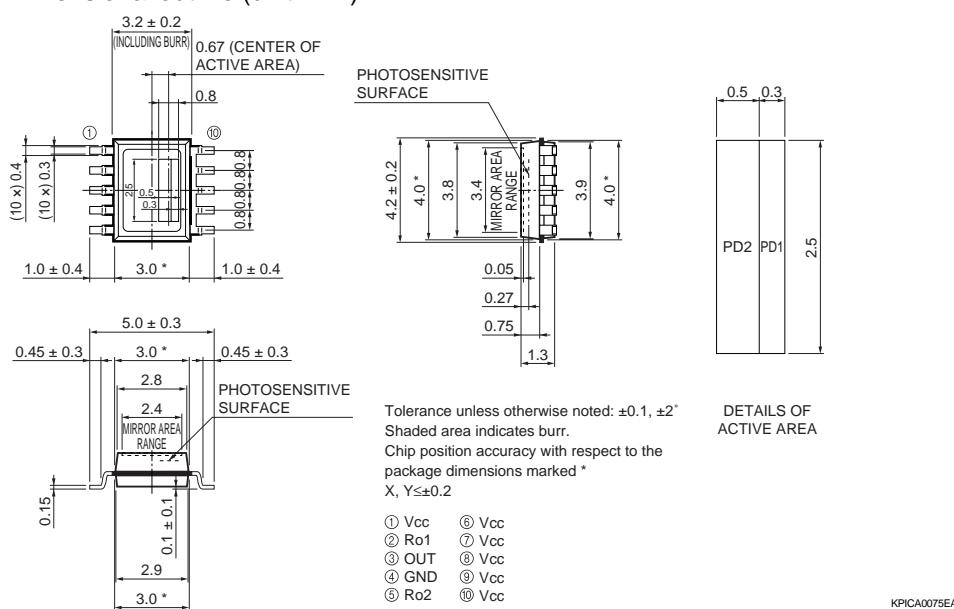
Pi: Input power [W]

Ro1, Ro2: External gain resistance [Ω]; usable range 1 kΩ to 10 kΩ

VRO1 and VRO2 are input to the internal comparator so the output Vo is "High" when VRO1 < VRO2 or "Low" when VRO1 > VRO2.

We recommend using S10456 under the operating conditions that VRO1 and VRO2 are 2 to 3 V.

■ Dimensional outline (unit: mm)



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